Weebit Nano reports excellent test results in preparation for the move to 300mm wafers at 28nm

14 January 2019 – Weebit Nano (ASX: WBT), the Israel-based semiconductor company seeking to develop and commercialise the next generation of memory technology, has reported successful endurance results of its ReRAM cells as a key step towards moving to 300mm wafers at 28nm. The ReRAM cells demonstrated stable voltage levels and endurance, at levels competitive to production non-volatile memories.

Weebit and its partner Leti, the French research institute recognised as a global leader in the field of micro-electronics, performed the tests which demonstrated Array-level endurance above 100,000 cycles, on par with expectation in the storage memory market, and a significant improvement over flash memories. In addition, Weebit ensured the SiOx ReRAM layer will be compatible with different tools and technologies used by different production fabs, which is crucial for transferring the Weebit technology to different commercial manufacturers.

Final characterisation will continue over coming weeks on array performance and extended endurance and retention in preparation for the migration to 300mm wafers at 28nm.

Coby Hanoch, CEO of Weebit Nano, said: "The baseline technical parameter improvement phase is a significant milestone towards commercialisation. Achieving production-level endurance and voltage results are key in this."

"We developed various compositions and process conditions which enable us to control the SiOx parameters, providing desired performance. This is crucial to achieve high yields and reliability across multiple fabs and products. This improved performance of lower voltage levels will easily integrate into advanced CMOS nodes for use in low power applications. The high endurance is well above the capability of Flash and very competitive in the market."

"In addition to technical parameter improvements, we also created a more flexible manufacturing base which will give us much more flexibility in future. We used different tools and technologies, used by different production fabs, so we later have the ability to choose which production fab(s) we prefer."

"We believe this progress ensures our ReRAM memories are very attractive for companies using leading-edge designs, including leading Artificial Intelligence and Internet of Things applications."

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About Weebit Nano Limited
Weebit Nano is a leader in the development of next generation computer memory technology, and plans to become the new industry standard in this space. Its goal is to address the growing need for a significantly higher performance and lower power computer memory technology. Weebit Nano's ReRAM technology is based on fab-friendly Silicon Oxide, allowing the company to rapidly execute, without the need for special equipment or preparations. The company secured several patents to ensure optimal commercial and legal protection for its ground-breaking technology.

Weebit Nano's technology enables a quantum leap, allowing semiconductor memory elements to be significantly cheaper, faster, more reliable and more energy efficient than the existing Flash technology. Weebit Nano has signed an R&D agreement with Leti, an R&D institute that specialises in nanotechnologies, to further develop SiOx ReRAM technology.

For more information please visit: www.weebit-nano.com